



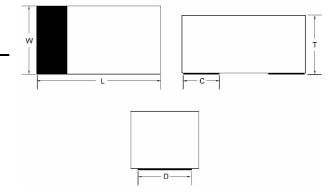
0.125 AMPS High Speed Switching Diode

1005



Features

- ♦ For surface mounted application
- ♦ Low forward voltage drop
- ♦ High Current capability
- ♦ Fast switching for high efficiency
- High surge current capability
- ♦ Chip version in 1005
- High temperature soldering: 260°C / 10 seconds at terminals



Mechanical Data

- ♦ Cases: 1005
- → Terminals: Gold plated, solderable per
- ♦ MIL-STD-750, method 2026,
- ♦ Polarity: indicated by cathode band
- ♦ Package code: RW
- ♦ Weight: 0.003 gram (approximately)

Item	1005		
пеш	1005		
L	0.102(2.60)		
	0.095(2.40)		
W	0.051(1.30)		
	0.043(1.10)		
T	0.035(0.90)		
	0.027(0.70)		
С	0.020(0.50)		
	Typical		
D	0.040(1.00)		
	Typical		

Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%

Type Number	Symbol	1005	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	VR	80	V
Maximum Average Forward Rectified Current Resistive Load f>50Hz	I _{F(AV)}	125	mA
Peak Forward Surge Current 8.3 ms	I _{FSM}	1.0	Α
Half Sine-wave 1 uS		2.0	Α
Maximum Instantaneous Forward Voltage @5 mA @100 mA	VF	0.72 1.0	V
Maximum D.C. Reverse Current VR=20V at Rated DC Blocking Voltage VR=80V	I _R	25 100	nA
Typical Reverse Recovery Time(Note 1) T _J =25 °C	Trr	9.0	nS
Junction Capacitance (Note 2)	Cj	9.0	pF
Power Dissipation	PD	200	mW
Operating Junction Temperature Range	TJ	-40 to + 125	°C
Storage Temperature Range	Тѕтс	-40 to + 125	°C

Notes:

- 1. Reverse Recovery Test Conditions: I_F=I_R=10mA, R_L=100 ohms, Irr=1mA.
- 2. Measured at 1 MHz and Applied Reverse Voltage of 0.5V D.C.